## 1 Characteristics

| Table 1. Compliant with the following standards |                           |                     |                                 |                     |  |  |  |  |
|---|---------------------------|---------------------|---------------------------------|---------------------|--|--|--|--|
| Standard  | Peak surge<br>voltage (V) | Voltage<br>waveform | Required<br>peak<br>current (A) | Current<br>waveform | Minimum<br>series resistor<br>Rs to meet<br>standard ( Ω ) |  |  |  |
| GR-1089 Core First level                        | 2500                      | 2/10 µs             | 500                             | 2/10 µs             | 12   |  |  |  |
| GR-1009 Core First level                        | 1000                      | 10/1000 µs          | 100                             | 10/1000 µs          | 10   |  |  |  |
| GR-1089 Core Second level                       | 5000                      | 2/10 µs             | 500                             | 2/10 µs             | 24   |  |  |  |
| GR-1089 Core Intra-building                     | 1500                      | 2/10 µs             | 100                             | 2/10 µs             | 0  |  |  |  |
|   | 6000                      |                     | 150                             |                     | 35   |  |  |  |
| ITU-T-K20/K21                                   | 4000                      | 10/700 µs           | 100                             | 5/310 µs            | 10   |  |  |  |
|   | 1500                      |                     | 37.5                            |                     | 0  |  |  |  |
| ITU-T-K20 (IEC61000-4-2)                        | 8000                      | 1/60 ns             | ESD contac                      |                     | 0  |  |  |  |
| 110-1-K20 (IEC61000-4-2)                        | 15000                     | 1/00 115            | ESD air discharge               |                     | 0  |  |  |  |
| IEC61000-4-5                                    | 4000                      | 10/700 µs           | 100                             | 5/310 µs            | 14   |  |  |  |
| IEC61000-4-3                                    | 4000                      | 1.2/50 µs           | 100                             | 8/20 µs             | 0  |  |  |  |
| TIA-068-A (formarly ECC part 69) type A         | 1500                      | 10/160 µs           | 200                             | 10/160 µs           | 20   |  |  |  |
| TIA-968-A (formerly FCC part 68) type A         | 800                       | 10/560 µs           | 100                             | 10/560 µs           | 15   |  |  |  |
| TIA-968-A (formerly FCC part 68) type B         | 1000                      | 9/720 µs            | 25                              | 5/320 µs            | 0  |  |  |  |

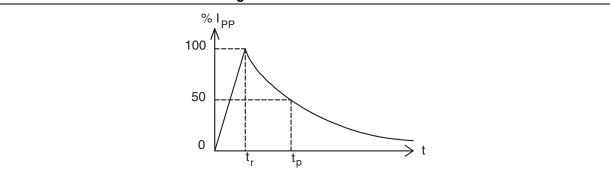
| Table 1 | Compliant with | the following | standards |
|---------|----------------|---------------|-----------|
|         | oompnant with  | the rono ming | Standards |

Table 2. Absolute maximum ratings ( $T_{amb} = 25 \text{ °C}$ )

| Symbol                             | Parameter   | Value                            | Unit            |    |
|------------------------------------|---|----------------------------------|-----------------|----|
| I <sub>PP</sub>                    | Peak pulse current  | 10/1000 µs<br>5/310 µs<br>2/10µs | 50<br>80<br>150 | A  |
| I <sub>TSM</sub>                   | $ \begin{array}{ll} \mbox{Non repetitive surge peak on-state current (F = 50 Hz)} & t_p = 0.2 \mbox{ s} \\ I_{TSM} \mbox{ value specified for each line} & t_p = 1 \mbox{ s} \\ I_{TSM} \mbox{ value can be applied on both lines at the same time} & t_p = 15 \mbox{ min.} \\ (GND \mbox{ capability is twice the line } I_{TSM}) &  \end{array} $ |                                  |                 | A  |
| V <sub>Gn</sub><br>V <sub>Gp</sub> | Negative battery voltage range<br>Positive battery voltage range  | -120 to 0<br>0 to +120           | V               |    |
| Тj                                 | Operating junction temperature range  | -40 to +125                      | °C              |    |
| T <sub>stg</sub>                   | Storage temperature range   | -55 to +150                      | °C              |    |
| ΤL                                 | Lead solder temperature (10 s duration)   |                                  | 260             | °C |



Figure 3. Pulse waveform



### Table 3. Thermal resistance

| Symbol               | Parameter           | Value | Unit |
|----------------------|---------------------|-------|------|
| R <sub>th(j-a)</sub> | Junction to ambient | 150   | °C/W |

### Table 4. Parameters related to the negative suppressor

| Symbol            | Parameter   | Test conditions   | Min. | Max.    | Unit |
|-------------------|---|---|------|---------|------|
| I <sub>Gn</sub>   | Negative gate trigger current                             | V <sub>Gn/GND</sub> = -60 V<br>Measured at 50 Hz  |      | 5       | mA   |
| I <sub>H-</sub>   | Holding current (see Figure 4)                            | V <sub>Gn</sub> = -60 V   | 150  |         | mA   |
| V <sub>DGL-</sub> | Dynamic switching voltage Gn / TIP or RING <sup>(1)</sup> | $\begin{split} V_{Gn/GND} &= -60 \text{ V} \\ 10/700 \ \mu\text{s} & 2 \ \text{kV}  \text{R}_{\text{s}} &= 25 \ \Omega  \text{I}_{\text{PP}} &= 30 \ \text{A} \\ 1.2/50 \ \mu\text{s} & 2 \ \text{kV}  \text{R}_{\text{s}} &= 25 \ \Omega  \text{I}_{\text{PP}} &= 30 \ \text{A} \end{split}$ |      | 8<br>12 | V    |
| V <sub>GnT</sub>  | G <sub>n</sub> to TIP voltage                             | I <sub>Gn</sub> = 20 mA   | 0.7  | 1.7     | V    |

1. The V<sub>DGL</sub> value is the difference between the peak line voltage during the surge and the programmed gate voltage.

### Table 5. Parameters related to the positive suppressor

| Symbol            | Parameter   | Test conditions   | Min. | Max.    | Unit |
|-------------------|---|---|------|---------|------|
| I <sub>Gp</sub>   | Positive gate trigger current                             | $V_{Gp/GND}$ = 60 V, measured at 50 Hz  |      | 5       | mA   |
| V <sub>DGL+</sub> | Dynamic switching voltage Gp / TIP or RING <sup>(1)</sup> | $V_{Gp/GND} = 60 V$<br>10/700 µs 2 kV $R_s = 25 \Omega$ $I_{PP} = 30 A$<br>1.2/50 µs 2 kV $R_s = 25 \Omega$ $I_{PP} = 30 A$ |      | 8<br>20 | V    |
| V <sub>GpR</sub>  | G <sub>P</sub> to RING voltage                            | I <sub>Gp</sub> = -20 mA  | 1    | 2       | V    |

1. The  $V_{DGL}$  value is the difference between the peak line voltage during the surge and the programmed gate voltage.

### Table 6. Parameters related to TIP or RING / GND

| Symbol         | Parameter                     | Test conditions   |  | Max.   | Unit |
|----------------|-------------------------------|---|--|--------|------|
| ۱ <sub>R</sub> | Reverse leakage current       | $V_{\text{TIP or RING}} = +120 \text{ V}  V_{\text{Gp/TIP or RING}} = +1 \text{ V}$ $V_{\text{TIP or RING}} = -120 \text{ V}  V_{\text{Gn/TIP or RING}} = -1 \text{ V}$ |  | 5<br>5 | μA   |
| С              | Capacitance TIP or RING / GND | $V_R$ = -3 V, F =1 MHz, $V_{Gp}$ = 60 V, $V_{Gn}$ = -60 V   |  | 60     | pF   |



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|                                 | Table I Recommended gute capacitance |      |      |      |    |  |  |  |
|---------------------------------|--------------------------------------|------|------|------|----|--|--|--|
| Symbol                          | Min.                                 | Тур. | Max. | Unit |    |  |  |  |
| C <sub>n</sub> , C <sub>p</sub> | Gate decoupling capacitance          |      | 220  |      | nF |  |  |  |

 Table 7. Recommended gate capacitance

### Figure 4. Relative variation of holding current versus junction temperature

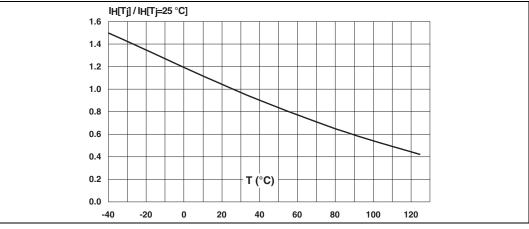


Figure 5. Maximum non repetitive surge peak on state current versus overload duration

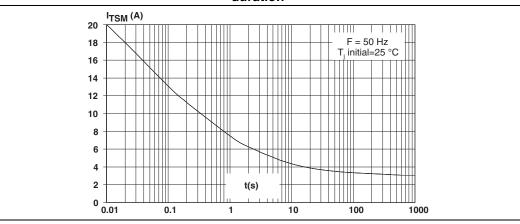
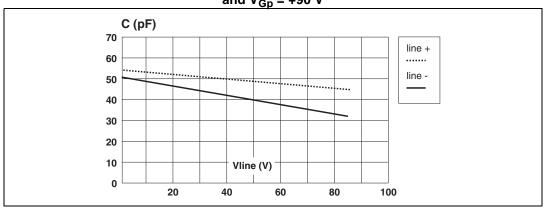


Figure 6. Capacitance versus reverse applied voltage (typical values) with V<sub>Gn</sub> = -90 V and V<sub>Gp</sub> = +90 V



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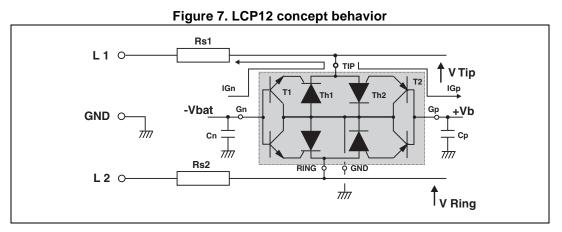
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#### LCP12

### 2 Technical information



*Figure 7* shows the classical protection circuit using the LCP12 crowbar concept. This topology has been developed to protect two-battery voltage SLICs. It allows both positive and negative firing thresholds to be programmed. The LCP12 has two gates (Gn and Gp). Gn is biased to negative battery voltage -Vbat, while Gp is biased to the positive battery voltage +Vb.

When a negative surge occurs on one wire (L1 for example), a current IGn flows through the base of the transistor T1 and then injects a current in the gate of the thyristor Th1 which turns-on. All the surge current flows through the ground. After the surge, when the current flowing through Th1 becomes less negative than the negative holding current  $I_{H-}$ , Th1 switches off. This holding current  $I_{H-}$  is temperature dependent as per *Figure 4* 

When a positive surge occurs on one wire (L1 for example), a current IGp flows through the base of the transistor T2 and then injects a current in the gate of the thyristor Th2 which fires. All the surge current flows through the ground. After the surge, when the current flowing through Th2 becomes less positive than the positive holding current  $I_{H+}$ , Th2 switches off. This holding current  $I_{H+}$ , typically 20 mA at 25 °C, is temperature dependent and the same *Figure 4* also applies.

The capacitors Cn and Cp are used to speed up the crowbar structure firing during the fast rise or fall edges. This allows minimization of the dynamic breakover voltage at the SLIC TIP and RING inputs during fast surges. Please note that these capacitors are generally available around the SLIC. To be efficient they have to be as close as possible to the LCP12 gate pins (Gn and Gp) and to the reference ground track (or plan). The optimized value for Cn and Cp is 220 nF.

The series resistors Rs shown in *Figure* 7 represent the fuse resistors or the PTCs which are needed to withstand the power contact or the power induction tests imposed by the country standards. Taking this factor into account, the actual lightning surge current flowing through the LCP12 is equal to:

I surge = Vsurge / (Rg + Rs)

With

V surge = peak surge voltage imposed by the standard.

Rg = series resistor of the surge generator

Rs = series resistor of the line card (e.g. PTC)



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For a line card with 50  $\Omega$  of series resistors which has to be qualified under GR-1089 1000 V 10/1000 µs surge, the present current through the LCP12 is equal to:

The LCP12 topology is particularly optimized for the new telecom applications such as fiber in the loop, WLL systems, and decentralized central office, for example.

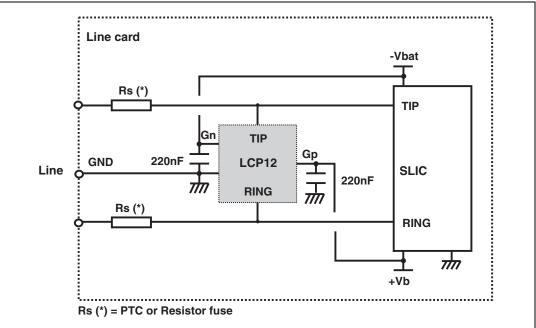


Figure 8. Protection of SLIC with positive and negative battery voltages

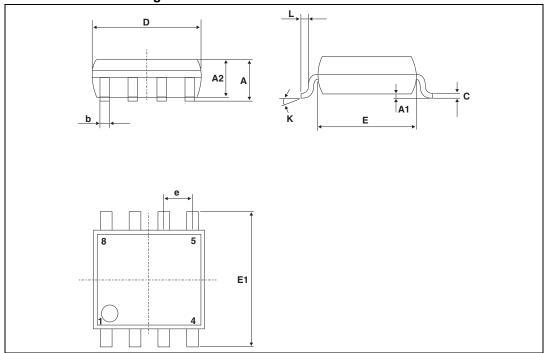
*Figure 8* shows the classical protection topology for SLIC using both positive and negative battery voltages. With such a topology the SLIC is protected against surge over +Vb and lower than -Vbat. In this case, +Vb can be programmed up to +120 V while -Vbat can be programmed down to -120 V.

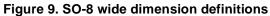


## 3 Package information

- Epoxy meets UL94, V0
- Lead-free package

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <u>www.st.com</u>. ECOPACK<sup>®</sup> is an ST trademark.



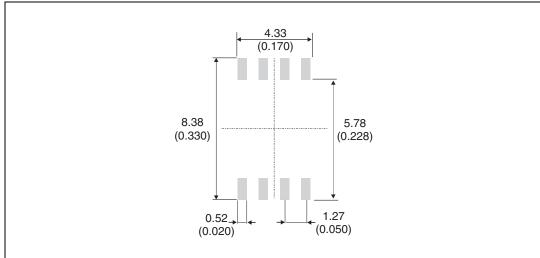




|      |      |             |      |        | ~     |      |  |  |
|------|------|-------------|------|--------|-------|------|--|--|
|      |      | Dimensions  |      |        |       |      |  |  |
| Ref. |      | Millimeters |      | Inches |       |      |  |  |
|      | Min. |             | Max. | Min.   |       | Max. |  |  |
| А    | 1.70 | 1.90        | 2.10 | 0.07   | 0.07  | 0.08 |  |  |
| A1   | 0.05 | 0.10        | 0.25 | 0.00   | 0.00  | 0.01 |  |  |
| A2   | 1.65 | 1.80        | 1.75 | 0.06   | 0.07  | 0.07 |  |  |
| b    | 0.38 | 0.43        | 0.48 | 0.01   | 0.02  | 0.02 |  |  |
| С    | 0.15 | 0.20        | 0.25 | 0.01   | 0.01  | 0.01 |  |  |
| D    | 5.14 | 5.24        | 5.34 | 0.02   | 0.021 | 0.21 |  |  |
| Е    | 5.20 | 5.30        | 5.40 | 0.02   | 0.021 | 0.21 |  |  |
| E1   | 7.70 | 7.80        | 8.25 | 0.30   | 0.031 | 0.32 |  |  |
| е    |      | 1.27        |      | 0.05   | 0.05  |      |  |  |
| K    |      |             | 8.00 | 0.14   | 0.31  |      |  |  |
| L    | 0.55 | 0.75        | 0.85 | 0.02   | 0.03  | 0.03 |  |  |

Table 8. SO-8 wide dimension values

### Figure 10. SO-8 wide footprint in mm (inches)





# 4 Ordering information

| Order code    | Marking | Package   | Weight | Base qty | Delivery mode |
|---------------|---------|-----------|--------|----------|---------------|
| LCP12-150B1RL | LCP12   | SO-8 wide | 0.125g | 1500     | Tape and reel |

## 5 Revision history

| Date        | Revision | Changes   |
|-------------|----------|---|
| 14-May-2010 | 1        | Initial release.  |
| 23-Feb-2012 | 2        | Updated dimensions in <i>Table 8</i> . Standardized nomenclature for Gn and Gp. |
| 18-Jun-2012 | 3        | Updated dimension D in SO-8 wide.   |
| 20-Mar-2014 | 4        | Updated Description, Table 6 and Package information formatting.                |



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